

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

2SC2877

DESCRIPTION

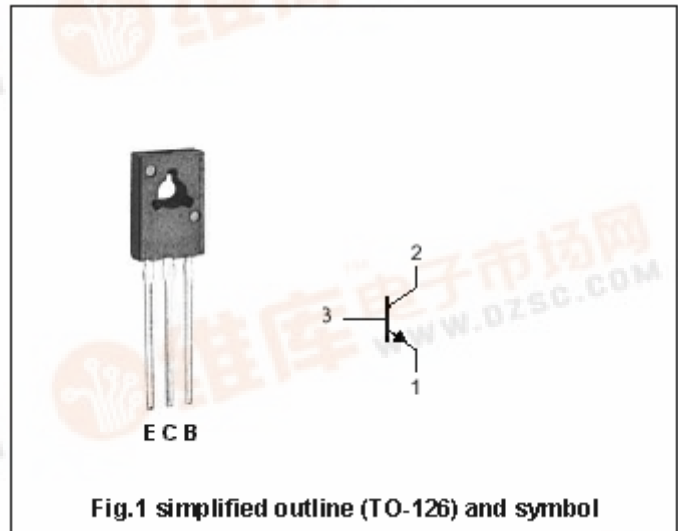
- With TO-126 package
- Complement to type 2SA1217
- Good linearity of h_{FE}

APPLICATIONS

- Audio frequency power amplifier
- Low speed switching
- Suitable for output stage of 5 watts car radio and car stereo

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	40	V
V_{CEO}	Collector-emitter voltage	Open base	40	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		3	A
I_B	Base current		1	A
P_D	Total power dissipation	$T_C=25^{\circ}C$	10	W
T_j	Junction temperature		150	$^{\circ}C$
T_{stg}	Storage temperature		-55~150	$^{\circ}C$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =10mA ; I _B =0	40			V
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =2.0A ; I _B =0.2A			0.8	V
V _{BE}	Base-emitter on voltage	I _C =0.5A ; V _{CE} =2V			1.0	V
I _{CBO}	Collector cut-off current	V _{CB} =40V ; I _E =0			0.1	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =5V ; I _C =0			0.1	μ A
h _{FE-1}	DC current gain	I _C =0.5A ; V _{CE} =2V	80		240	
h _{FE-2}	DC current gain	I _C =2.5A ; V _{CE} =2V	25			
f _T	Transition frequency	I _C =0.5A ; V _{CE} =2V		100		MHz

◆ h_{FE-1} Classifications

O	Y
80-160	120-240

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PACKAGE OUTLINE

